



PATENT  
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:  
Natsuki KUSHIYAMA  
Serial No: 09/887,875  
Filed: June 22, 2000  
For: Semiconductor Components Industries, Ltd.

Art Unit: 2181

Examiner: Not Assigned

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to:  
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**TRANSMITTAL OF INFORMATION**  
**DISCLOSURE STATEMENT**

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Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

JAN 22 2004

## Technology Center 2100

Dear Sirs:

1.  The information disclosure statement submitted herewith is being filed within three months of the filing date of the application other than a continued prosecution application, or within three months of the date of entry into the national stage of an international application, or before the mailing date of a first Office Action on the merits, or before the mailing of a first Office action after the filing of a request for continued examination under §1.114, whichever event occurs last. 37 C.F.R. §1.97(b).
2.  The information disclosure statement transmitted herewith is being filed *after* the period specified in §1.97(b), but *before* the mailing date of a final action under §1.113, or a notice of allowance under §1.311, or an action that otherwise closes prosecution in the application, whichever occurs first. A statement specified in §1.97(e) or a fee set forth in §1.17(p) is included. 37 C.F.R. §1.97(c). 

**§1.97(e) STATEMENT**

I, the person signing below, state:

that each item of information contained in the information disclosure statement was first cited in the attached communication from a foreign patent office in a counterpart foreign application and that the communication is dated not more than three months prior to the filing of the statement. 37 C.F.R. §1.97(e)(1).

OR

that no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in



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~~§1.56(c)~~ more than three months prior to the filing of the statement. 37 C.F.R. §1.97(e)(2).

OR FEE

Attached is a fee set forth in 37 C.F.R. §1.17(p) for submission of an information disclosure statement under §1.97(c). (\$180.00). [OR:] Please charge the fee set forth in 37 C.F.R. §1.17(p) for submission of an information disclosure statement under §1.97(c) (\$180.00) to Deposit Account No. 50-1314. A copy of this petition is enclosed.

3.  The information disclosure statement transmitted herewith is being filed *after* the period specified in §1.97(c), but before, or simultaneously with the payment of the issue fee. A statement specified in §1.97(e) and a fee set forth in §1.17(p) are included. 37 C.F.R. §1.97(d).

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§1.97(e) STATEMENT

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I, the person signing below, state:

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that each item of information contained in the information disclosure statement was first cited in the attached communication from a foreign patent office in a counterpart foreign application and that the communication is dated not more than three months prior to the filing of the statement. 37 C.F.R. §1.97(e)(1).

OR

that no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in §1.56(c) more than three months prior to the filing of the statement. 37 C.F.R. §1.97(e)(2).

AND FEE

Attached is a fee set forth in 37 C.F.R. §1.17(p) for submission of an information disclosure statement under §1.97(d). (\$180.00).

4.  If it should be determined that for any reason either an insufficient fee or an excessive has been paid, please charge any insufficiency or credit any overpayment necessary to ensure consideration of the information disclosure statement for the above-identified application to Deposit Account No. 50-1314. A copy of this petition is enclosed.

5.  A list of 3 reference(s) is in the enclosed Form PTO-1449.

**NON-ENGLISH LANGUAGE REFERENCES**

- Enclosed is an Office Action for a counterpart application.
- The specification incorporates comments on the relevancy of Non-English language references.
- Set forth below are comments provided by the applicant's home country counsel on the relevancy of non-English language references:

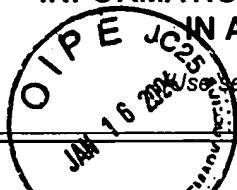
Respectfully submitted,  
HOGAN & HARTSON L.L.P.

By:   
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Registration No. 41,232  
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Date: January 13, 2004

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FORM PTO-1449	Docket Number (Optional) 81790.0204	Application Number 09/887,875
<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>	Applicant Natsuki KUSHIYAMA	
<i>(Use several sheets if necessary)</i>	Filing Date June 22, 2001	Group Art Unit 2181



## U.S. PATENT DOCUMENTS

**RECEIVED**

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## FOREIGN PATENT DOCUMENTS

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

	SUZUKI, et al., "Analytical Surface Potential Expression for Double Gate SOI MOSFET," International Workshop on VLSI Process and Device Modeling, pp. 150-151 (May 14-15, 1999)
	YOO, et al., "Double Gate Poly Si TFT," Fourth Asian Symposium on Information Display, pp. 219-222 (Feb. 13-14, 1997)
	WONG, et al., "Double Gate SOI MOSFET," International Electron Device Meeting, 15, 2.1-4 (December 1998)

EXAMINER	DATE CONSIDERED
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